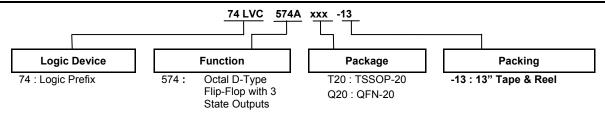


### **Ordering Information**



Part Number	Package	Package	Package	Package 13" Tape and Reel		
Part Number	Code	(Note 4 & 5)	Size	Quantity	Part Number Suffix	
74LVC574AT20-13	T20	TSSOP-20	6.4mm X 6.5mm X 1.2mm 0.65 mm lead pitch	2500/Tape & Reel	-13	
74LVC574AQ20-13	Q20	V-QFN4525-20	2.5mm X 4.5mm X 0.95mm 0.50 mm lead pitch	2500/Tape & Reel	-13	

Notes:

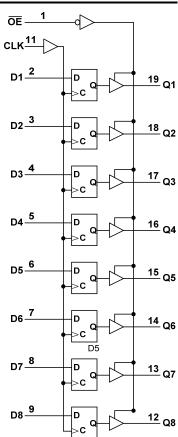
- 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

  5. V-QFN4525-20 is a JEDEC recognized naming convention that specifies the package thickness category as V and the number 4525 describes the package as 4.5mm X 2.5mm.

### **Pin Descriptions**

Pin Number	Pin Name	Description
1	ŌE	Output Enable
2	D1	Data Input
3	D2	Data Input
4	D3	Data Input
5	D4	Data Input
6	D5	Data Input
7	D6	Data Input
8	D7	Data Input
9	D8	Data Input
10	GND	Ground
11	CLK	Clock
12	Q8	Latch Output
13	Q7	Latch Output
14	Q6	Latch Output
15	Q5	Latch Output
16	Q4	Latch Output
17	Q3	Latch Output
18	Q2	Latch Output
19	Q1	Latch Output
20	Vcc	Supply Voltage

### **Logic Diagram**



### **Function Table**

	(Each Latch)							
	INPUTS	3	OUTPUT					
OE	CLK	D	Q					
L	$\uparrow$	Н	Н					
L	<b>↑</b>	L	L					
L	H or L	Х	$Q_0$					
Η	Χ	Χ	Z					



### Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
Vcc	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0V	-20	mA
lok	Output Clamp Current V <sub>O</sub> < 0V	-50	mA
lo	Continuous Output Current -0.5V < V <sub>O</sub> V <sub>CC</sub> +0.5V	±50	mA
Icc	Continuous Current Through V <sub>CC</sub>	100	mA
I <sub>GND</sub>	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
P <sub>TOT</sub>	Total Power Dissipation	500	mW

- 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

### **Recommended Operating Conditions** (Note 8)

Symbol	Parameter	Conditions	Min	Max	Unit
\/	Cumply Voltage	Operating	1.65	3.6	V
$V_{CC}$	Supply Voltage	Data Retention Only	1.5	_	V
VI	Input Voltage	_	0	5.5	V
Vo	Output Voltage	_	0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.65V	_	-4	
	High Lavel Output Compant	V <sub>CC</sub> = 2.3V	_	-8	^
I <sub>OH</sub>	High-Level Output Current	V <sub>CC</sub> = 2.7V	_	-12	mA
		V <sub>CC</sub> = 3.0V	_	-24	
		V <sub>CC</sub> = 1.65V	_	4	
	Law Lawal Output Compant	V <sub>CC</sub> = 2.3V	_	8	^
l <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 2.7V	_	12	mA
		V <sub>CC</sub> = 3.0V	_	24	
Δt/ΔV	Input Transition Rise or Fall Rate		_	10	ns/V
T <sub>A</sub>	Operating Free-Air Temperature		-40	+125	°C

Note:

8. Unused inputs should be held at  $V_{\text{CC}}$  or Ground.



## **Electrical Characteristics**

Symbol	Parameter	Test Conditions	V	T <sub>A</sub> = -40°C	to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
Symbol	Parameter	rest Conditions	Vcc	Min	Max	Min	Max	Unit
			1.65V to 1.95V	V <sub>CC</sub> X 0.65	_	V <sub>CC</sub> X 0.65	_	
$V_{IH}$	High-Level Input Voltage		2.3V to 2.7V	1.7	_	1.7	_	V
	voltago		3.0V to 3.6V	2	_	2	_	
	Lave Lavel Immed		1.65V to 1.95V	_	V <sub>CC</sub> X 0.35	_	V <sub>CC</sub> X 0.35	
$V_{IL}$	Low-Level Input Voltage		2.3V to 2.7V	_	0.7	_	0.7	V
	voltago		3.0V to 3.6V	_	0.8	_	0.8	
		$I_{OH} = -50 \mu A$	1.65V to 3.6V	V <sub>CC</sub> -0.2	_	V <sub>CC</sub> -0.3	_	
		$I_{OH} = -4mA$	1.65V	1.2	_	1.05	_	
$V_{OH}$	High-Level	I <sub>OH</sub> = -8mA	2.3V	1.7	_	1.65	_	
VOH	Output Voltage		2.7V	2.2	_	2.05	_	V
		$I_{OH} = -12mA$	3.0V	2.4	_	2.48	_	V
		I <sub>OH</sub> = -24mA	3.0V	2.3	_	2.0	_	
		I <sub>OL</sub> = 100μA	1.65V to 3.6V	_	0.2	_	0.3	
		I <sub>OL</sub> = 4mA	1.65V	_	0.45	_	0.65	
$V_{OL}$	Low-Level Output Voltage	I <sub>OL</sub> = 8mA	2.3V	_	0.60	_	0.80	V
		I <sub>OL</sub> = 12mA	2.7V	_	0.40	_	0.60	
		I <sub>OL</sub> = 24mA	3.0V	_	0.55	_	0.80	
l <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 0$ or 5.5V	0V	_	±10	_	20	μΑ
II	Input Current Control Pins	V <sub>I</sub> = GND or 5.5V	0 to 3.6V	_	±5	_	±20	μΑ
loz	Z-State Current including Input Current I/O Pins	$V_1 = GND \text{ or } 5.5V$ $V_0 = 0 \text{ to } 5.5V$	3.6V	_	±5	_	±20	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	3.6V	_	10	_	40	μA
$\Delta I_{CC}$	Additional Supply Current	One Input at $V_{CC}$ -0.6V $I_{O}$ = 0A	2.7V to 3.6V	_	500	_	5000	μA
Ci	Input	Control Pins $V_1 = GND \text{ or } V_{CC}$	0V to 3.6V	4.0 typical		4.0 typical		pF
O <sub>I</sub>	Capacitance	I/O Pins	0 V 10 0.0 V	5.5 ty	/pical	5.5 typical		ρı



## **Switching Characteristics**

Symbol	Parameter	Test Conditions	Vcc		T <sub>A</sub> = +25°(	<b>C</b>		10°C to 5°C		40°C to	Unit
		Conditions		Min	Тур	Max	Min	Max	Min	Max	
			1.8V ± 0.15V	35	40		35		30		
r	Maximum F	Figure 1	2.5V ± 0.2V	50	60		50		45		Mhz
f <sub>MAX</sub>	Frequency		2.7V	80	100		80		64		IVITIZ
			3.3V ± 0.3V	100	125		100		80		
			1.8V ± 0.15V	5.0	2.5		5.0		5.5		
4	Pulse Width	Figure 1	2.5V ± 0.2V	4.0	2.0		4.0		4.5		
t <sub>W</sub>	CLK		2.7V	3.3	1.7		3.3		3.5		ns
			3.3V ± 0.3V	3.0	1.5		3.0		3.5		
			1.8V ± 0.15V	4.0	2.0		4.0		4.5		
	Set-up Time D <sub>N</sub>	Figure 1	2.5V ± 0.2V	3.0	1.5		3.0		3.5		1
tsu	to CLK	·	2.7V	2.0	1.0		2.0		2.5		ns
			3.3V ± 0.3V	2.0	1.0		2.0		2.5		
			1.8V ± 0.15V	3.0	1.5		3.0		3.5		
	t <sub>H</sub> Hold Time D <sub>N</sub> to CLK	Figure 1	2.5V ± 0.2V	2.0	1.0		2.0		2.5		ns
tн			2.7V	1.5	1.0		1.5		2.0		
			3.3V ± 0.3V	1.5	1.0		1.5		2.0		
			1.8V ± 0.15V	1.0	6.0	15.1	1.0	15.7	1.0	16.9	
	Propagation Delay	Figure 1	2.5V ± 0.2V	1.0	3.9	8.8	1.0	9.0	1.0	10.5	
t <sub>PD</sub>	CLK to Q <sub>N</sub>	Ü	2.7V	1.0	4.2	8.1	1.0	9.4	1.0	10.0	ns
	CLN 10 QN		3.3V ± 0.3V	1.5	3.8	7.1	1.5	7.6	1.5	8.1	
			1.8V ± 0.15	1.0	7.8	16.5	1.0	17.0	1.0	18.4	
	Enable Time	Einen 4	2.5V ± 0.2V	1.0	4.0	9.0	1.0	9.5	1.0	10.5	
t <sub>EN</sub>	OE to Q <sub>N</sub>	Figure 1	2.7V	1.0	4.4	8.3	1.0	8.5	1.0	10.0	ns
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9.0	
			1.8V ± 0.15V	1.0	7.8	16.5	1.0	17.0	1.0	18.4	
	Disable Time	E	2.5V ± 0.2V	1.0	4.0	9.0	1.0	9.5	1.0	10.5	
t <sub>DIS</sub>	$\overline{OE}$ to $Q_N$	Figure 1	2.7V	1.0	4.4	8.3	1.0	8.5	1.0	10.0	ns
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9.0	
			1.8V ± 0.15V	1.0	7.8	16.5	1.0	17.0	1.0	18.4	
	Disable Time	Fig. 4	2.5V ± 0.2V	1.0	4.0	9.0	1.0	9.5	1.0	10.5	ns
tDIS	t <sub>DIS</sub>	Figure 1	2.7V	1.0	4.4	8.3	1.0	8.5	1.0	10.0	
	"		3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9.0	1
tsk(0)	Output Skew Time		3.3V ± 0.3V			1.0				1.5	ns

# **Operating Characteristics**

T<sub>A</sub> = +25°C

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Тур	Unit	
	C <sub>pd</sub> Power dissipation capacitance per gate		1.8V ± 0.15V	9.9		
$C_{pd}$		F = 10 MHz	2.5V ± 0.2V	10.2	pF	
			3.3V ± 0.3V	10.6		



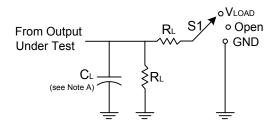
# Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	TSSOP-20	(Note 9)	_	74	_	°C/W
$\theta_{JC}$	Thermal Resistance Junction-to-Case	TSSOP-20	(Note 9)	_	15	_	°C/W
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	V-QFN4525-20	(Note 9)	_	67	_	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	V-QFN4525-20	(Note 9)	_	20	_	°C/W

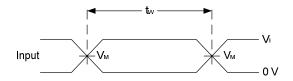
Note: 9. Test conditions for TSSOP-20 and V-QFN4525-20: Devices mounted on 4 layer FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout per JESD 51-7.



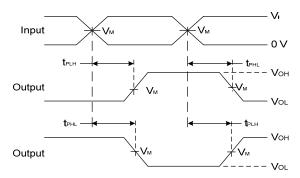
### **Parameter Measurement Information**



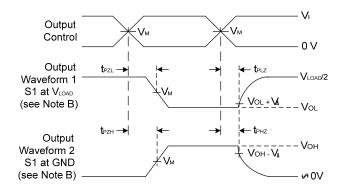
,,	Inputs		.,	, , , , , , , , , , , , , , , , , , ,					
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	V <sub>LOAD</sub>	CL	RL	<b>V</b> Δ		
1.8V ± 0.15V	V <sub>CC</sub>	≤ 2ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	30pF	1ΚΩ	0.15V		
2.5V ± 0.2V	V <sub>CC</sub>	≤ 2ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	30pF	500Ω	0.15V		
2.7V	2.7V	≤ 2.5ns	1.5V	6V	50pF	500Ω	0.3V		
3.3V ± 0.3V	2.7V	≤ 2.5ns	1.5V	6V	50pF	500Ω	0.3V		



### Voltage Waveform Pulse Duration



**Voltage Waveform Propagation Delay Times** Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

- Notes: A. Includes test lead and test apparatus capacitance.

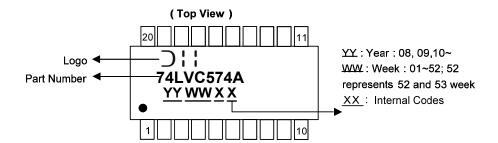
  - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
    C. Inputs are measured separately one transition per measurement.
  - D.  $t_{\text{PLZ}}$  and  $t_{\text{PHZ}}$  are the same as  $t_{\text{dis.}}$
  - E.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{EN0}}$
  - F. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>.

Figure 1 Load Circuit and Voltage Waveforms



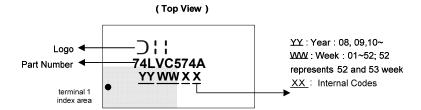
### **Marking Information**

#### (1) TSSOP20



Part Number	Package
74LVC574AT20	TSSOP-20

#### (2) QFN-20 (V-QFN4525-20)



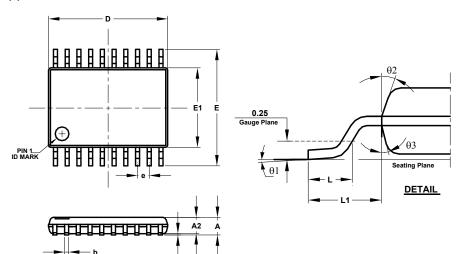
Part Number	Package
74LVC574AQ20	V-QFN4525-20



### **Package Outline Dimensions**

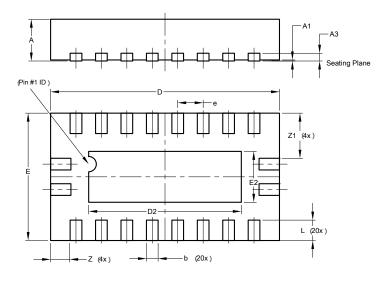
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### (1) TSSOP-20



TSSOP-20					
Dim	Min	Max	Тур		
Α	-	1.20	-		
A1	0.05	0.15	-		
A2	0.80	1.05	ı		
b	0.19	0.30	-		
С	0.09	0.20	-		
D	6.40	6.60	6.50		
Е	6.20	6.60	6.40		
E1	4.30	4.50	4.40		
е	0.65 BSC				
L	0.45	0.75	0.60		
L1	1.0 REF				
θ1	0°	8°	-		
θ2	10°	14°	12°		
θ3	10°	14°	12°		
All Dimensions in mm					

#### (2) QFN-20 (V-QFN4525-20)



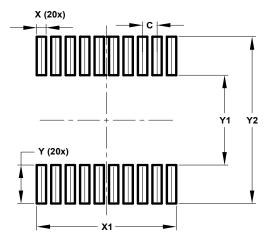
V-QFN4525-20				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	-	-	0.15	
b	0.18	0.30	0.23	
D	4.45	4.55	4.50	
D2	2.85	3.15	3.00	
Е	2.45	2.55	2.50	
E2	0.85	1.15	1.00	
е	0.50BSC			
L	0.30	0.50	0.40	
Z	-	-	0.385	
<b>Z</b> 1	-	-	0.885	
All Dimensions in mm				



### **Suggested Pad Layout**

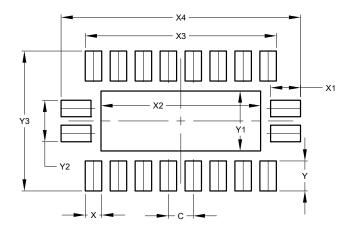
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### (1) TSSOP-20



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	6.270
Υ	1.789
Y1	4.160
Y2	7.720

#### (2) QFN-20 (V-QFN4525-20)



Dimensions	Value (in mm)
С	0.500
Х	0.330
X1	0.600
X2	3.200
Х3	3.830
X4	4.800
Υ	0.600
Y1	1.200
Y2	0.830
V3	2 800



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